L Number	Hits	Search Text	DB .	Time stamp
- Talliber	244	vacuum near microelectronic and electron	USPAT:	2004/05/10
		adj emitter	US-PGPUB:	07:32
			EPO; JPO;	
			DERWENT:	
			IBM_TDB	
2	49	vacuum adj microelectronic near device	USPAT:	2004/05/10
-	70	and electron near emitter and substrate	US-PGPUB:	07:39
		and electric near field	EPO; JPO;	
		and electric field field	DERWENT:	
			IBM TDB	
3	4	("5773921"   "5855675"   "5892231"	USPAT	2004/05/10
•	-	"6512235").PN.	USFAI	07:36
4	3	("5089742"   "5138220"   "5495143").PN.	USPAT	2004/05/10
•	3	( 3003742   3130220   3433143 J.FN.	037.41	07:37
.	6	vacuum adj microelectronic and electron	USPAT:	2004/05/10
5	ь	near emitter and applying adj electric near	US-PGPUB:	07:46
		field	EPO: JPO:	07,40
		Tiela	DERWENT:	
			IBM TDB	
.	8	("4041346"   "4272699"   "4301369"	USPAT	2004/05/10
6	8		USPAI	07:42
		"5395774"   "5583393"   "5726524"   "5773921"   "5872422").PN.		07:42
7	10102	vacuum adj microelectronicnear device	USPAT;	2004/05/10
		and electron near emitter and	US-PGPUB;	07:50
		29/\$.ccls.applying adj electric near field	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
В	9	vacuum adj microelectronicnear device	USPAT;	2004/05/10
		and electron near emitter and 29/\$.ccls.	US-PGPUB;	07:48
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
9	0	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and applying adj electric near	US-PGPUB;	07:51
		field and 250/\$.ccls.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
10	3	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and applying adj electric near	US-PGPUB;	07:52
		field and 313/\$.ccls.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
11	0	microelectronic near device and electron	USPAT;	2004/05/10
,	•	near emitter and applying adj electric near	US-PGPUB;	07:52
		field and 437/\$.ccls.	EPO; JPO;	
			DERWENT;	
			IBM TDB	

12	112	microelectronic near device and electron	USPAT:	2004/05/10
12	112	near emitter and electric near field	USPAT;	07:53
		near emitter and electric near field		07:55
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
13	62	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and electric near field and	US-PGPUB;	07:53
		313/\$.ccls.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
14	31	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and electric near field and	US-PGPUB;	07:55
		445/\$.ccis.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
15	80	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and electric near field and	US-PGPUB;	07:56
		(445/51; 445/50 ; 445/24 ; 445/49 ; 313/495 ;	EPO; JPO;	
		313/496	DERWENT;	
		; 313/497 ; 313/306 ; 313/307 ;	IBM_TDB	
		313/308 ; 313/309 ; 313/310		
		; 313/311).ccls.		
16	0	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and electric near field and	US-PGPUB;	07:57
		29/\$.ccis. and 313/\$.ccis. and 445/\$.ccis.	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
17	8	microelectronic near device and electron	USPAT;	2004/05/10
		near emitter and electric near field and	US-PGPUB;	07:57
		313/\$.ccis. and 445/\$.ccis.	EPO; JPO;	
			DERWENT;	
			IBM TDB	
20	4	("5773921"   "5855675"   "5892231"	USPAT	2004/05/10
		"6512235").PN.		07:59